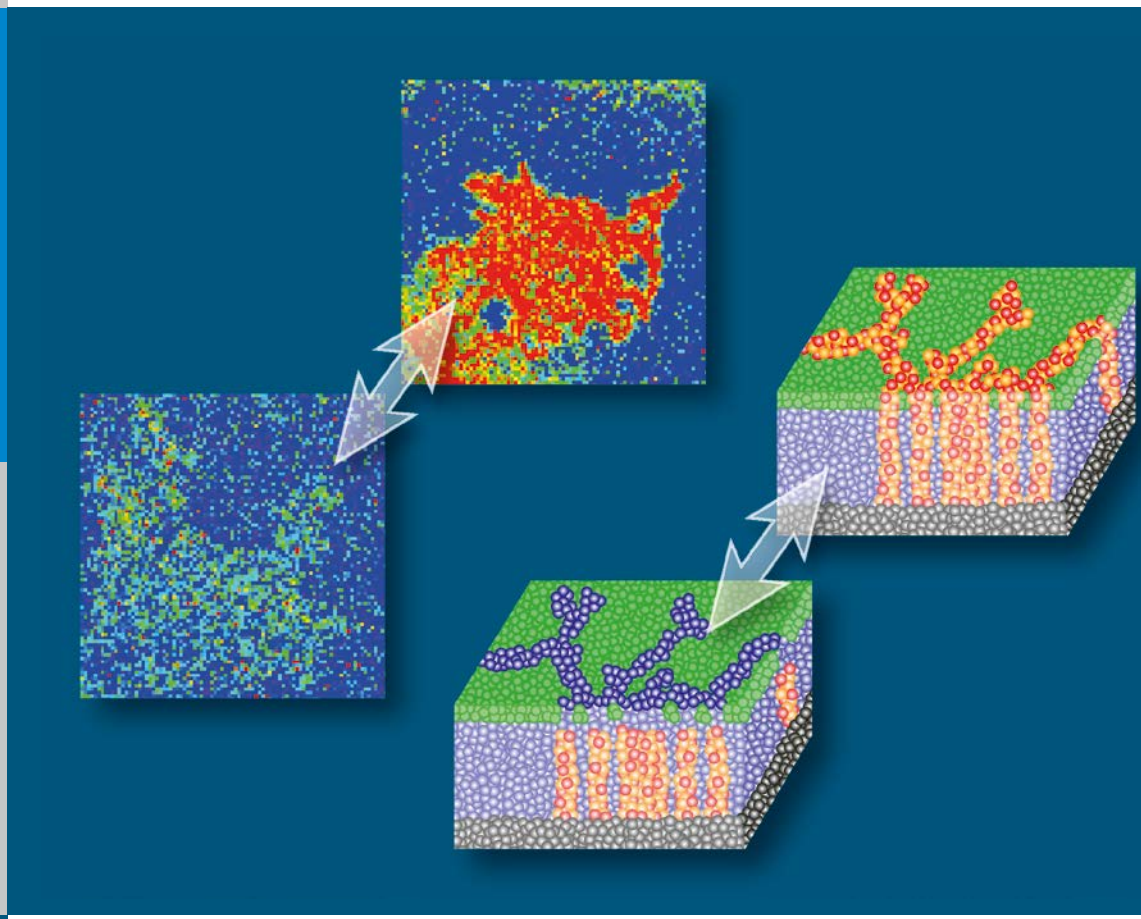
Redox processes and ionic transport in resistive switching binary metal oxides

Katharina Skaja



Information
Band / Volume 49
ISBN 978-3-95806-236-8

JÜLICH
FORSCHUNGSZENTRUM

Forschungszentrum Jülich GmbH
Peter Grünberg Institute (PGI)
Electronic Materials (PGI-7)

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Schriften des Forschungszentrums Jülich
Reihe Information / Information Band / Volume 49

ISSN 1866-1777 ISBN 978-3-95806-236-8

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